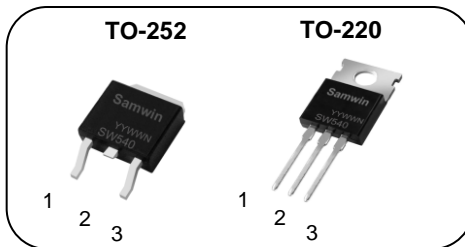


## N-channel Enhanced mode TO-252/TO-220 MOSFET

### Features

- High ruggedness
- Low  $R_{DS(ON)}$  (Typ 32m $\Omega$ )@ $V_{GS}=10V$
- Low Gate Charge (Typ 48nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application: Synchronous Rectification, Li Battery Protect Board, Inverter.

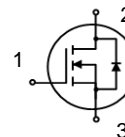


1. Gate 2. Drain 3. Source

$BV_{DSS}$  : 100V

$I_D$  : 32A

$R_{DS(ON)}$  : 32m $\Omega$



### General Description

This power MOSFET is produced with advanced technology of SAMWIN.

This technology enable the power MOSFET to have better characteristics, including fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics.



### Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW D 540	SW540	TO-252	REEL
2	SW P 540	SW540	TO-220	TUBE

### Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-252	TO-220	
$V_{DSS}$	Drain to source voltage	100		V
$I_D$	Continuous drain current (@ $T_C=25^\circ C$ )	32*		A
	Continuous drain current (@ $T_C=100^\circ C$ )	20*		A
$I_{DM}$	Drain current pulsed (note 1)	128		A
$V_{GS}$	Gate to source voltage	$\pm 20$		V
$E_{AS}$	Single pulsed avalanche energy (note 2)	117		mJ
$E_{AR}$	Repetitive avalanche energy (note 1)	12		mJ
dv/dt	Peak diode recovery dv/dt (note 3)	5		V/ns
$P_D$	Total power dissipation (@ $T_C=25^\circ C$ )	83	125	W
	Derating factor above 25 $^\circ C$	0.7	1.0	W/ $^\circ C$
$T_{STG}, T_J$	Operating junction temperature & storage temperature	-55 ~ + 150		$^\circ C$

\*. Drain current is limited by junction temperature.

### Thermal characteristics

Symbol	Parameter	Value		Unit
		TO-252	TO-220	
$R_{thjc}$	Thermal resistance, Junction to case	1.5	1.0	$^\circ C/W$
$R_{thja}$	Thermal resistance, Junction to ambient		56.7	$^\circ C/W$

Electrical characteristic (  $T_C = 25^\circ\text{C}$  unless otherwise specified )

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
<b>Off characteristics</b>						
$BV_{DSS}$	Drain to source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	100			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown voltage temperature coefficient	$I_D=250\mu A$ , referenced to $25^\circ\text{C}$		0.1		$V/^\circ\text{C}$
$I_{DSS}$	Drain to source leakage current	$V_{DS}=100V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=80V, T_C=125^\circ\text{C}$			50	$\mu A$
$I_{GSS}$	Gate to source leakage current, forward	$V_{GS}=20V, V_{DS}=0V$			100	nA
	Gate to source leakage current, reverse	$V_{GS}=-20V, V_{DS}=0V$			-100	nA
<b>On characteristics</b>						
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
$R_{DS(ON)}$	Drain to source on state resistance	$V_{GS}=10V, I_D=16A$		32	40	$m\Omega$
		$V_{GS}=10V, I_D=32A$		34	42	
$G_{fs}$	Forward transconductance	$V_{DS}=10V, I_D=16A$		63		S
<b>Dynamic characteristics</b>						
$C_{iss}$	Input capacitance	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$		2900		pF
$C_{oss}$	Output capacitance			144		
$C_{rss}$	Reverse transfer capacitance			104		
$t_{d(on)}$	Turn on delay time	$V_{DS}=50V, I_D=32A, R_G=25\Omega, V_{GS}=10V$ (note 4,5)		31		ns
$t_r$	Rising time			55		
$t_{d(off)}$	Turn off delay time			131		
$t_f$	Fall time			48		
$Q_g$	Total gate charge	$V_{DS}=80V, V_{GS}=10V, I_D=32A$ (note 4,5)		48		nC
$Q_{gs}$	Gate-source charge			13		
$Q_{gd}$	Gate-drain charge			12.5		
$R_g$	Gate resistance	$V_{DS}=0V$ , Scan F mode		1.5		$\Omega$

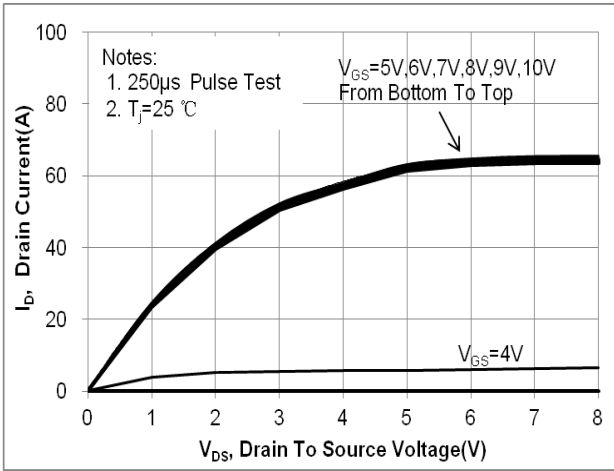
### Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			32	A
$I_{SM}$	Pulsed source current				128	A
$V_{SD}$	Diode forward voltage drop.	$I_S=32A, V_{GS}=0V$			1.4	V
$t_{rr}$	Reverse recovery time	$I_S=32A, V_{GS}=0V,$ $di_f/dt=100A/\mu s$		54		ns
$Q_{rr}$	Reverse recovery charge				111	nC

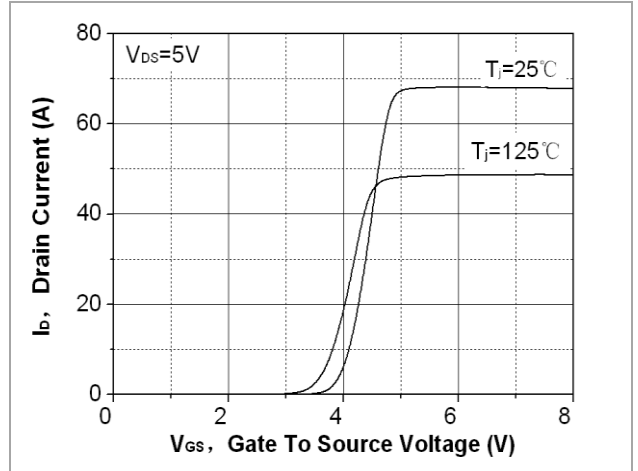
※. Notes

1. Repeattive rating : pulse width limited by junction temperature.
2.  $L = 1.04\text{mH}, I_{AS} = 15A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 32A, di/dt = 100A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
5. Essentially independent of operating temperature.

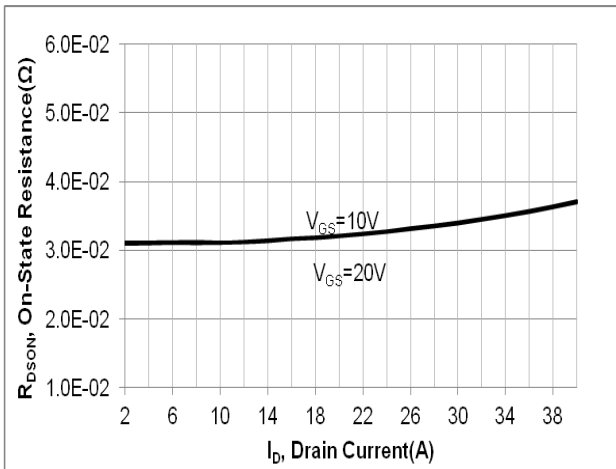
**Fig. 1. On-state characteristics**



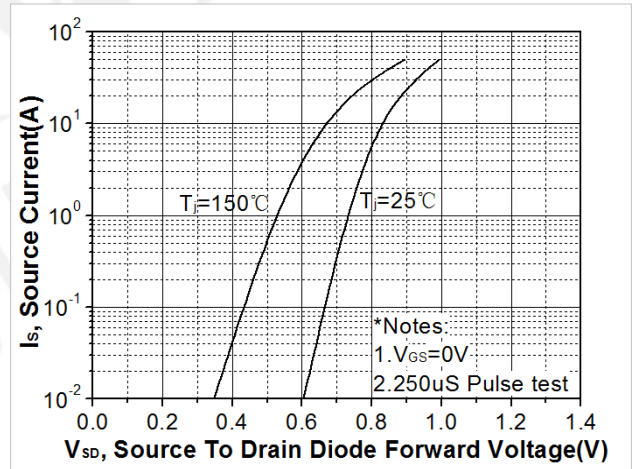
**Fig. 2. Transfer Characteristics**



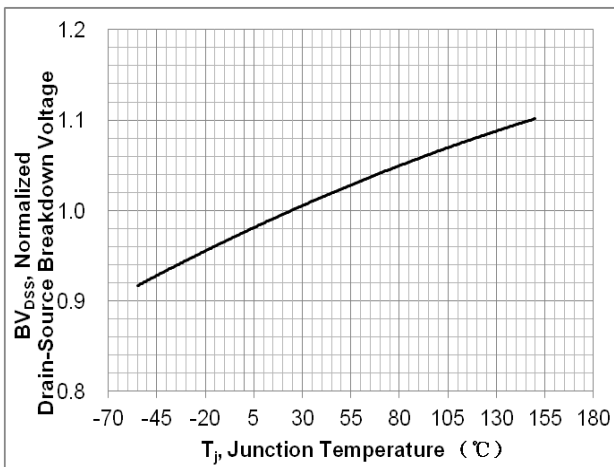
**Fig. 3. On-resistance variation vs. drain current and gate voltage**



**Fig. 4. On-state current vs. diode forward voltage**



**Fig 5. Breakdown voltage variation vs. junction temperature**



**Fig. 6. On-resistance variation vs. junction temperature**

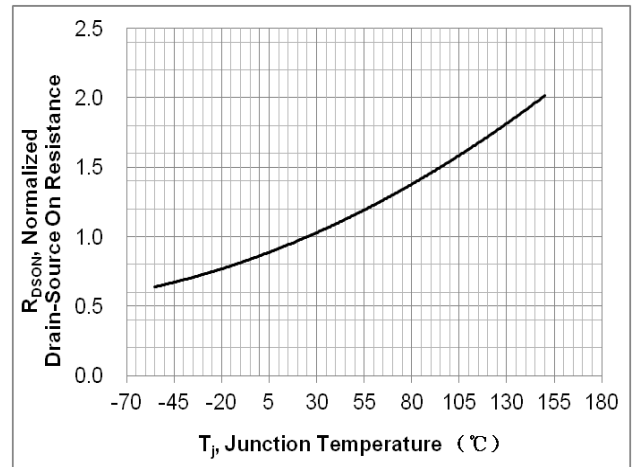


Fig. 7. Gate charge characteristics

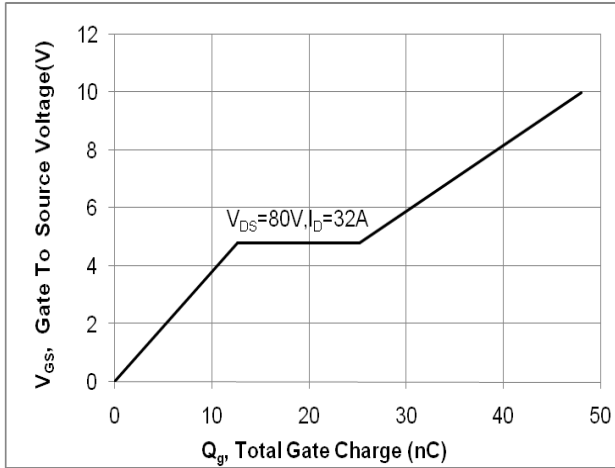


Fig. 8. Capacitance Characteristics

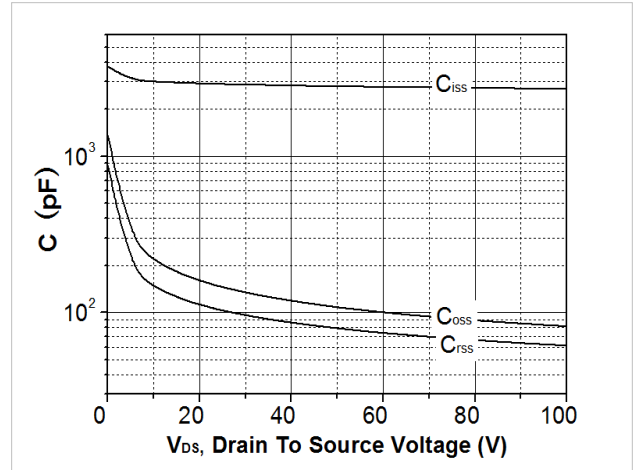


Fig. 9. Maximum safe operating area(TO-252)

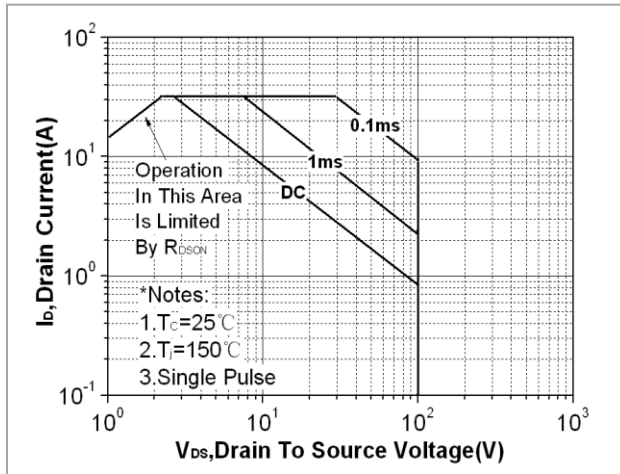


Fig. 10. Maximum safe operating area(TO-220)

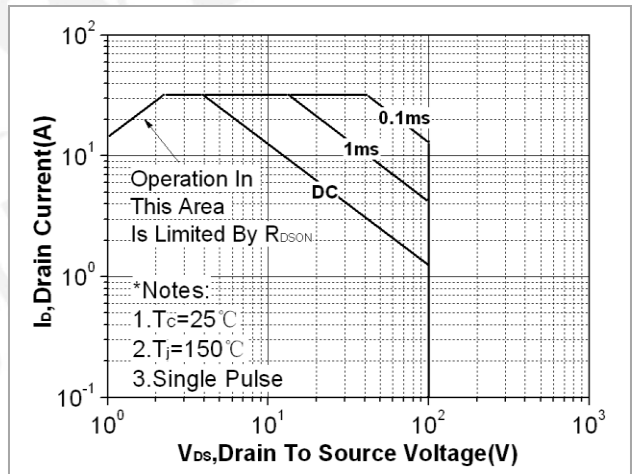


Fig. 11. Transient thermal response curve(TO-252)

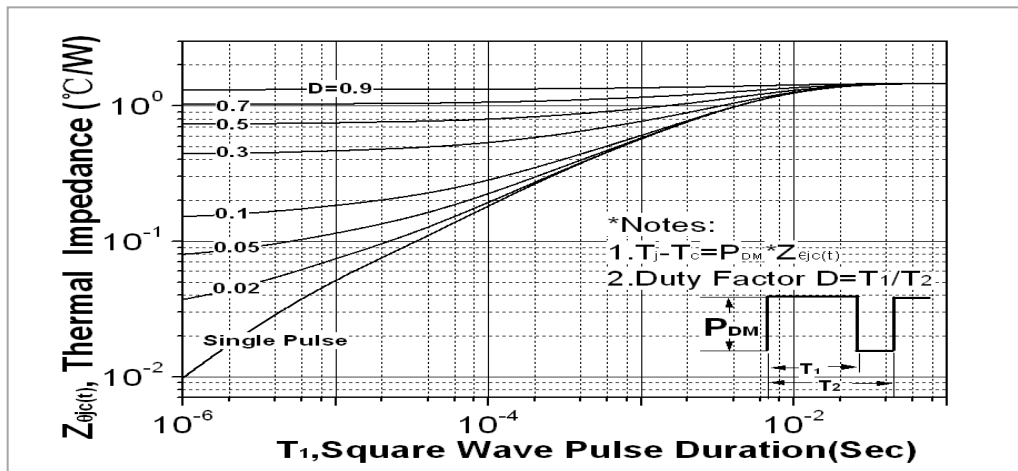


Fig. 12. Transient thermal response curve(TO-220)

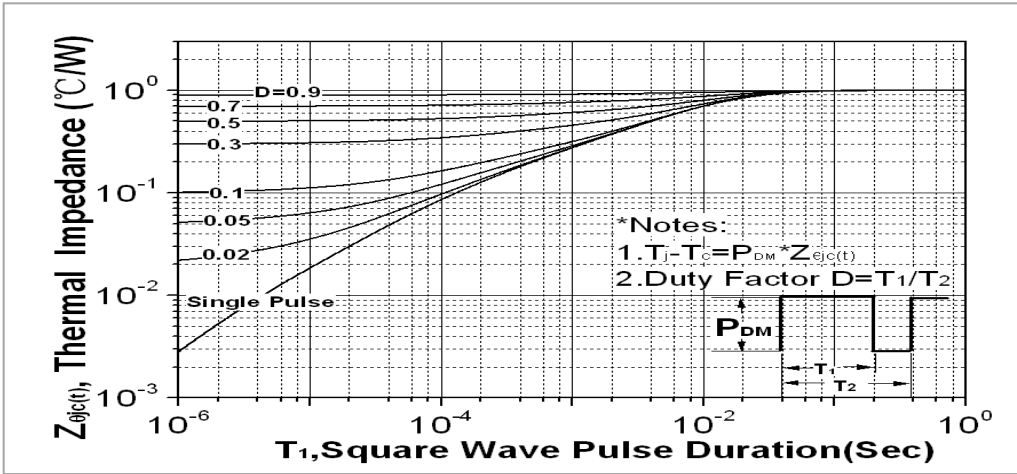


Fig. 13. Gate charge test circuit & waveform

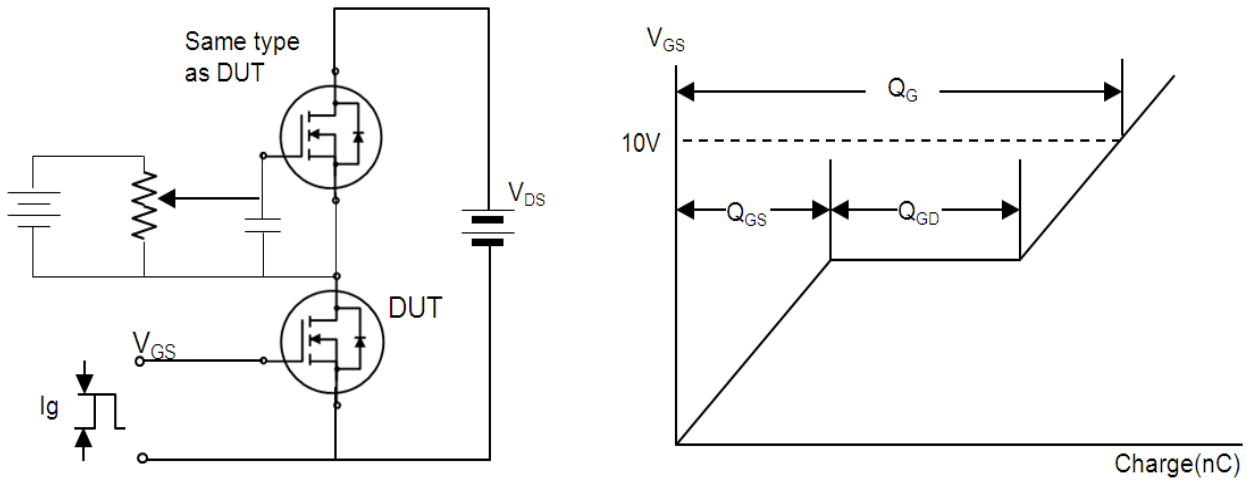


Fig. 14. Switching time test circuit & waveform

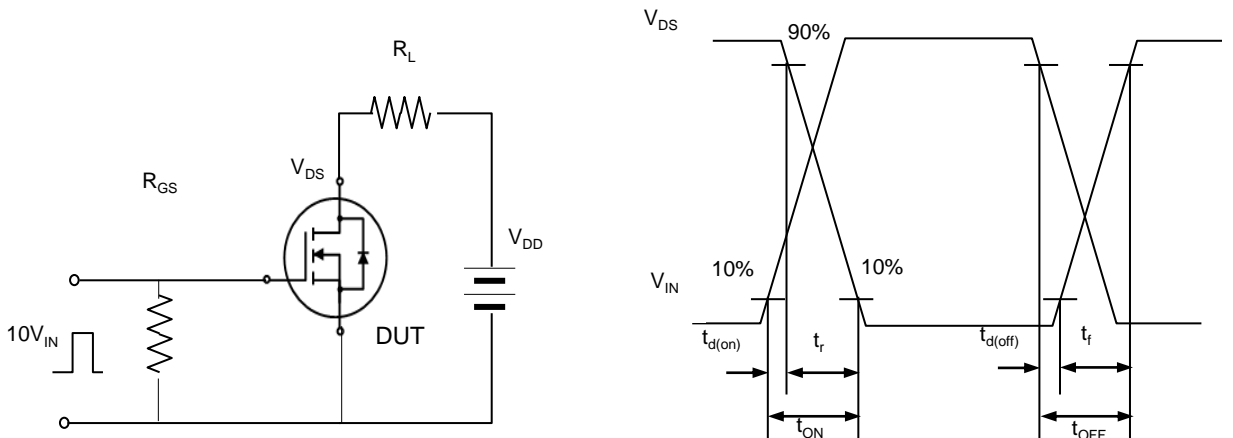


Fig. 15. Unclamped Inductive switching test circuit & waveform

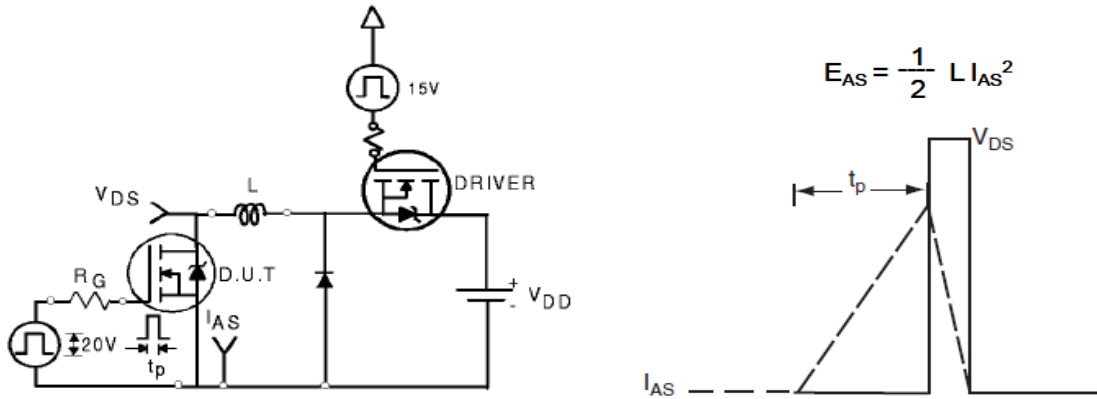
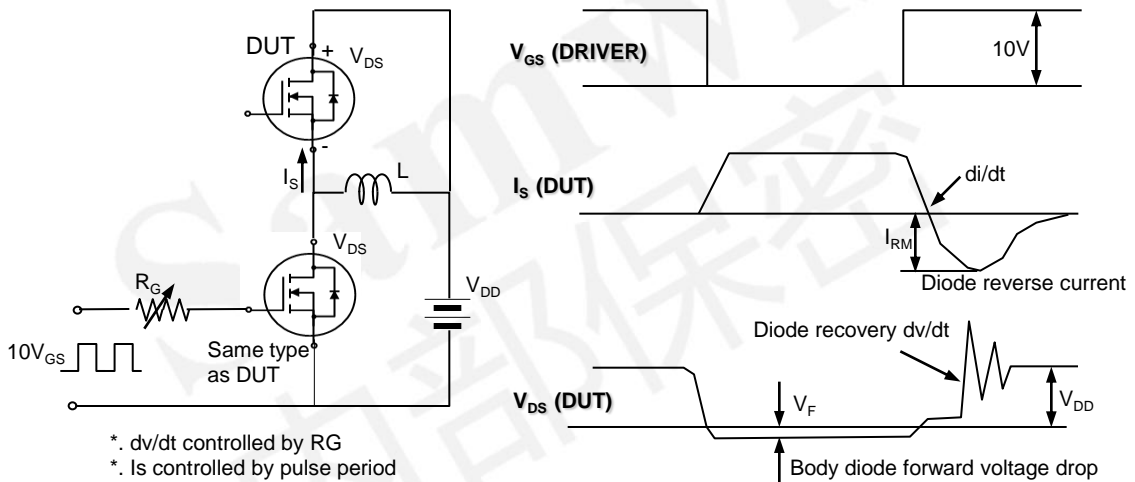


Fig. 16. Peak diode recovery dv/dt test circuit & waveform



## DISCLAIMER

\* All the data & curve in this document was tested in XI' AN SEMIPOWER TESTING & APPLICATION CENTE R.

\* This product has passed the PCT,TC,HTRB,HTGB,HAST,PC and Solderdunk reliability test

\* Qualification standards can also be found on the Web site (<http://www.semipower.com.cn>)

\* Suggestions for improvement are appreciated, Please send your suggestions to [samwin@samwinsemi.com](mailto:samwin@samwinsemi.com)